

beyond boundaries...

## 65A, 1200V STANDARD SCRS THYRISTOR

#### **DESCRIPTION:**



The ALPTS6512T80 is an 65A, 1200V Standard SCRS Thyristor and it Low on-state voltage device in small package with Highly dv/dt.

## **FEATURES:**

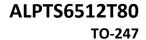
- Arr I<sub>T(RMS)</sub> = 65A, V<sub>DRM</sub>/V<sub>RRM</sub> = 1200V, I<sub>GT</sub> = 80mA
- ➤ Highly dv/dt.
- Small package
- Low on-state voltage
- RoHS compliant & halogen-free.
- Suffix "-H" indicated Halogen Free part, ex. ALPTS6512T80-H

#### **APPLICATIONS:**

- Domestic lighting.
- Domestic heating.
- Motor speed controllers.

## **MECHANICAL CHARACTERISTICS**

- > Epoxy: UL94-V0 rated flame retardant.
- Case: Molded plastic, TO-247
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position: Any.





## **MAXIMUM RATINGS**

MAXIMUM RATINGS @ T <sub>A</sub> = 25 °C unless otherwise specified				
PARAMETER	CONDITION	SYMBOL	RATINGS	UNIT
RMS on-state current (full sine wave)	T <sub>C</sub> =100°C	I <sub>T(RMS)</sub>	65	А
Non repetitive surge peak on-state current	F=50HZ, t=10ms	I <sub>TSM</sub>	650	А
I <sup>2</sup> t value for fusing	T <sub>P</sub> =10ms	I <sup>2</sup> t	1250	A <sup>2</sup> s
Critical rate of rise of on-state current	F=60HZ, T <sub>j</sub> =125°C	di/dt	100	A/μs
Peak gate current	T <sub>P</sub> =20μs, T <sub>j</sub> =125°C	I <sub>GM</sub>	8	А
Average gate power dissipation	T <sub>j</sub> =125°C	P <sub>G(AV)</sub>	1	W
Operating Junction Temperature Range			-40 to +125	°C
Storage Temperature Range			-40 to +150	°C



## ELECTRICAL CHARACTERISTICS @ TA = 25 °C unless otherwise specified

PARAMETER	CONDITIONS	SYMBOL	VALUE	UNIT
Gate trigger current	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A	I <sub>GT</sub>	≤80	mA
Gate trigger voltage	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A	V <sub>GT</sub>	≤1.5	V
Holding current	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A	I <sub>H</sub>	≤150	mA
Latching current	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A	IL	≤90	mA
Rise of off- state voltage	$V_D=67\%V_{DRM}$	dv/dt	≥400	V/μS
Peak on-state voltage	I <sub>T</sub> =130A	V <sub>TM</sub>	≤1.7	٧
Peak repetitive forward	$V_{RRM}=V_{DRM}$ , $T_j=25$ °C	I <sub>DRM</sub>	≤10	μΑ
blocking current	$V_{RRM}=V_{DRM}$ , $T_j=150$ °C	I <sub>RRM</sub>	≤4	mA

THERMAL RESISTANCES				
PARAMETER	SYMBOL	VALUE	UNIT	
Junction to case (AC)	$R_{th(j-c)}$	0.27	°C/W	



# TYPICAL DEVICE RATING AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)

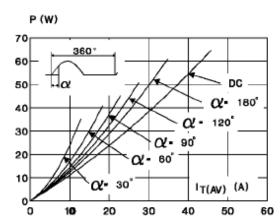


Fig.1 MAXIMUM POWER DISSIPATION VS. AVERAGE ON-STATE CURRENT

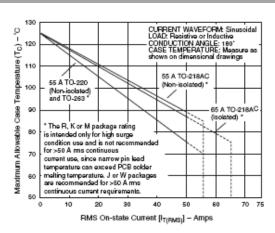


Fig.2 I<sub>T(AV)</sub> ON-STATE CURRENT VS. T<sub>L</sub>

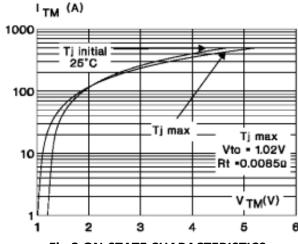


Fig.3 ON-STATE CHARACTERISTICS

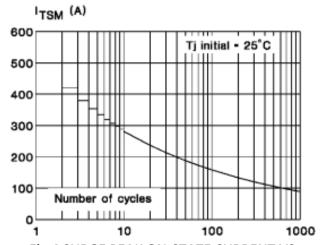


Fig.4 SURGE PEAK ON-STATE CURRENT VS.
NUMBER CYCLES

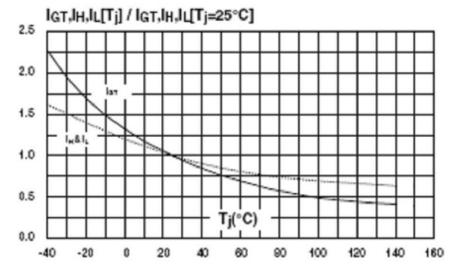
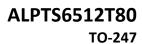


Fig.5 RELATIVE VARIATION OF GATE TRIGGER CURRENT, HOLDING CURRENT AND LATCHING CURRENT VS. JUNCTION TEMPERATURE (TYPICAL VALUE)



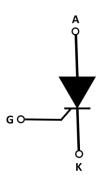


## **PINNING INFORMATION**

## SIMPLIFIED OUTLINE

## **SCHEMATIC DIAGRAM**

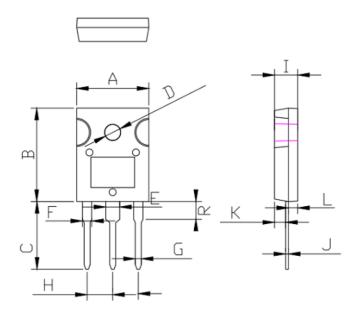






## **PACKAGE INFORMATION**

## TO-247



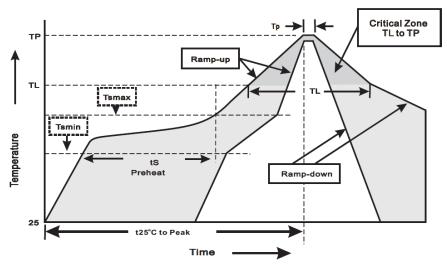
	OUTLINE DIMENSIONS					
CVAADOL	MILLIMETE		RS	RS INCHES		
SYMBOL	MIN	TYP.	MAX	MIN	TYP.	MAX
Α	15.45	15.50	15.55	0.608	0.610	0.612
В	19.90	20.00	20.10	0.783	0.787	0.791
С	14.40	14.50	14.60	0.567	0.571	0.575
D	3.30	3.50	3.60	0.130	0.138	0.142
Е	2.95	3.00	3.05	0.116	0.118	0.120
F	1.95	2.00	2.05	0.077	0.079	0.081
G	1.20	1.30	1.40	0.047	0.051	0.055
Н	5.40	5.50	5.60	0.213	0.217	0.220
I	4.95	5.00	5.05	0.195	0.197	0.199
J	0.58	0.60	0.62	0.023	0.024	0.024
K	2.30	2.40	2.50	0.091	0.094	0.098
L	1.90	2.00	2.10	0.075	0.079	0.083
R	3.60	3.80	4.00	0.142	0.150	0.157

beyond boundaries...

## **SOLDERING PARAMETERS**

#### SUGGESTED THERMAL PROFILES FOR SOLDERING PROCESSES

- 1. Storage environment: Temperature=5 °C~40 °C Humidity=55% ±25%
- 2. Reflow soldering of surface-mount devices



#### 3. Reflow soldering

PROFILE FEATURE	SOLDERING CONDITION
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3 °C/sec
Preheat	
- Temperature Min (T <sub>smin</sub> )	150 °C
- Temperature Max (T <sub>smax</sub> )	200 °C
- Time (min to max) (ts)	60 ~ 120 sec
T <sub>smax</sub> to T <sub>L</sub>	
- Ramp-upRate	<3 °C/sec
Time maintained above:	
- Temperature (T <sub>L</sub> )	217 °C
- Time(tL)	60 ~ 260 sec
Peak Temperature (T <sub>P</sub> )	255 °C-0/+5 °C
Time within 5 °C of actual Peak	10 ~ 30 sec
Temperature(tP)	
Ramp-down Rate	<3 °C/sec
Time 25 °C to Peak Temperature	<6 minutes



#### **CUSTOMER NOTE:**

#### **DISCLAIMER**

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- 1. ALPINESEMI™ Semiconductor Devices are RoHS compliant and hence customers are requested to dispose as per the prevailing Environmental Legislation put forth in their specific country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).



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